IN THE CLAIMS:

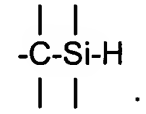
Please amend the claims as follows:

1-10. (Canceled)

11. (Previously Presented) A method comprising depositing on a substrate a plurality of layers, wherein the plurality of layers comprises one low dielectric constant oxidized organosilane layer comprising carbon, wherein the low dielectric constant oxidized organosilane layer is deposited in a plasma enhanced process from a mixture comprising an organosilane compound and an oxidizing gas and the carbon content of the low dielectric constant oxidized organosilane layer is from 1% to 50% by atomic weight, a layer selected from the group consisting of parylene, FSG, and silicon oxide layers, and a top layer of the plurality of layers that is a photoresist.

12. (Previously Presented) The method of claim 11, wherein the low dielectric constant oxidized organosilane layer is between two dielectric layers in the plurality of layers.

13. (Previously Presented) The method of claim 11, wherein the low dielectric constant oxidized organosilane layer is deposited in the presence of RF power and the organosilane compound includes the structure:



14. (Canceled)

15. (Previously Presented) A method comprising depositing on a substrate a plurality of layers, wherein one or more of the layers is a low dielectric constant oxidized organosilane layer comprising carbon, wherein the low dielectric constant oxidized

organosilane layer is deposited in a plasma enhanced process from a mixture comprising a methylsilane compound and an oxidizing gas, the carbon content of the low dielectric constant oxidized organosilane layer is from 1% to 50% by atomic weight, and a top layer of the plurality of layers is a photoresist.

16. (Original) The method of claim 15, wherein the plurality of layers further comprises a layer selected from the group consisting of parylene, FSG, silicon oxide, and silicon nitride layers.

17. (Currently Amended) The method of claim 15, wherein the plurality of layers comprises two low dielectric constant oxidized organosilane layers and an etch stop layer adjacent to both of the two low dielectric constant oxidized organosilane layers.

18. (Original) The method of claim 17, wherein the etch stop layer is a silicon oxide or silicon nitride layer.

19-20. (Canceled)

21. (Previously Presented) The method of claim 15, wherein the methylsilane compound has the formula $SiH_n(CH_3)_{4-n}$, where n=1 to 3 or $Si_2H_m(CH_3)_{6-m}$, where m=1 to 5.

22. (Previously Presented) The method of claim 15, further comprising etching the low dielectric constant oxidized organosilane layer using fluorine, carbon, and oxygen ions.

23. (Previously Presented) The method of claim 15, wherein the plurality of layers comprises one low dielectric constant oxidized organosilane layer comprising carbon.

24. (Previously Presented) The method of claim 23, wherein the low dielectric constant oxidized organosilane layer comprising carbon is between two dielectric layers in the plurality of layers.

25. (Currently Amended) The method of claim 15, wherein the methylsilane compound is methyl silane (CH_3SiH_3).

26. (Previously Presented) The method of claim 15, wherein the oxidizing gas is selected from the group consisting of O_2 and N_2O.

27. (Previously Presented) The method of claim 15, wherein the low dielectric constant oxidized organosilane layer is deposited in the presence of RF power.

28. (Previously Presented) The method of claim 15, further comprising etching a pattern in the plurality of layers.